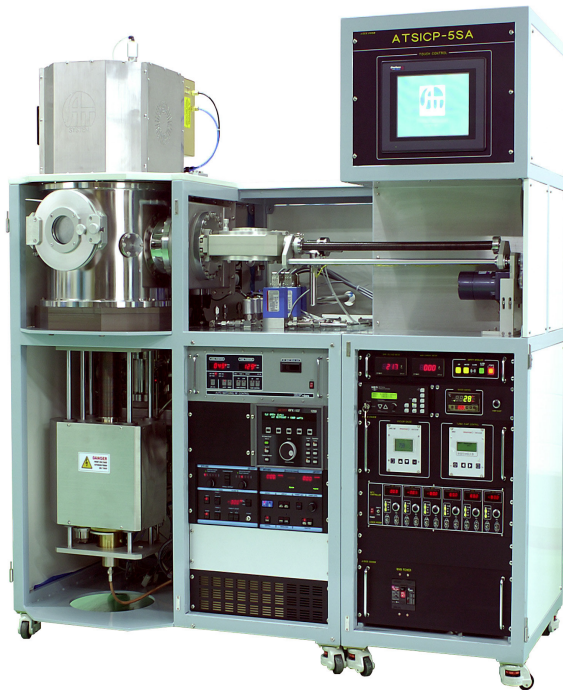
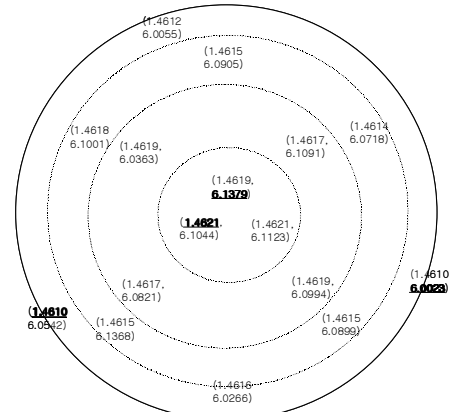


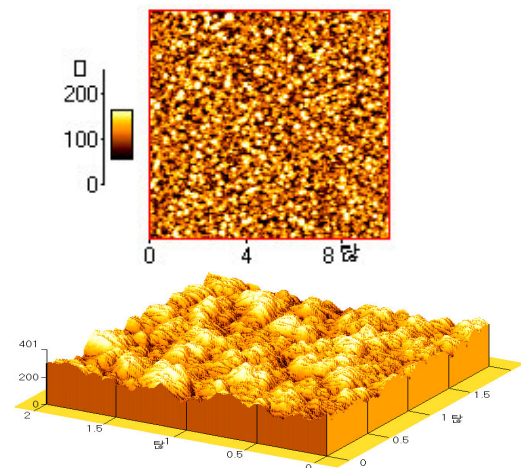
ATS-CVD Series PECVD System with High Density Plasma



Prism coupler analysis



AFM analysis

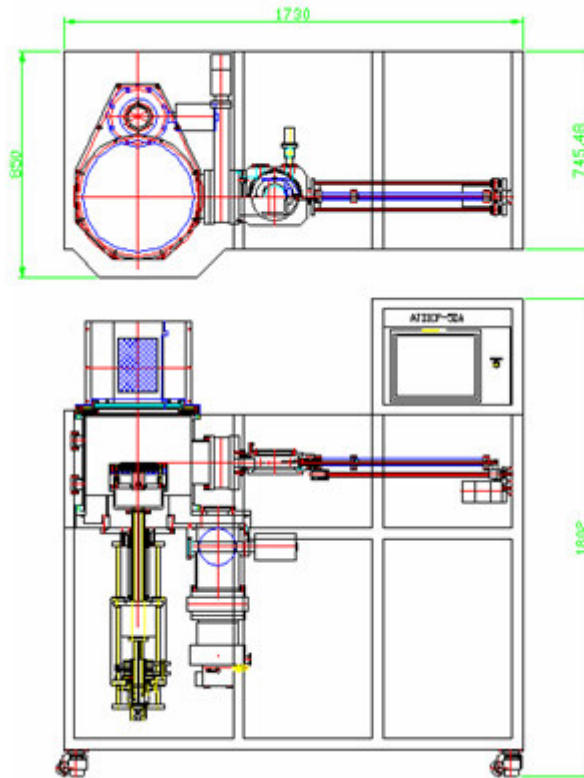


Special Features

- ◆ SiO₂ PECVD system for R&D and small scale production
- ◆ Excellent thickness and reflective index uniformity in deposited layer (ave. 7μm)
- ◆ Highly smooth surface
(RMS roughness of deposited layer : 30.6 Å)
- ◆ Transformer coupled high density plasma
- ◆ Applications
 - Optical waveguide
 - Passivation layer
- ◆ Wafer capacity
1 × 4"

- ◆ Average throughput
Up to 5,000 wafers per year
- ◆ Dimension : 1730L × 1277H × 725W (mm³)
- ◆ Others
 - Power : AC 1.2kW for TCP source
(13.56MHz)
 - AC 600W for bias voltage
(13.56MHz)
 - Gas : SiH₄ / O₂
 - Susceptor material : graphite
 - Heater : silicon carbide
(heating rate: 40°C/min,
max. temp.: 800°C, temp.
deviation : negligible)
 - Pump : rotary(600l/min) & turbo(500l/s)

◇ Layout



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